NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF392** is a Common Emitter Device Designed for Class A , AB and C Amplifier Applications in the 300 - 500 MHz Military Communications Band.

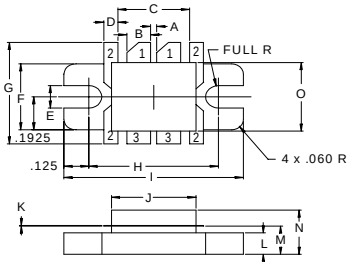
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Input Matching

MAXIMUM RATINGS

I_C	16 A
V_{CB}	60 V
P_{DISS}	270 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	.65 °C/W

PACKAGE STYLE .400 8L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.030 / 0.76	
B	.115 / 2.92	.125 / 3.18
C	.360 / 9.14	
D	.065 / 1.65	.075 / 1.91
E	.130 / 3.30	
F	.380 / 9.65	.390 / 9.91
G	.735 / 18.67	.765 / 19.43
H	.645 / 16.38	.655 / 16.64
I	.895 / 22.73	.905 / 22.99
J	.420 / 10.67	.430 / 10.92
K	.003 / 0.08	.007 / 0.18
L	.120 / 3.05	.130 / 3.30
M	.159 / 4.04	.175 / 4.45
N		.280 / 7.11
O	.395 / 10.03	.405 / 10.29

1 = COLLECTOR 2 = EMITTER
3 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 50 mA	30			V
BV_{CES}	I_C = 50 mA	60			V
BV_{EBO}	I_E = 5.0 Ma	4.0			V
I_{CBO}	V_{CB} = 30 V			5.0	mA
C_{ob}	V_{CB} = 28 V f = 1.0 MHz		52		pF
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	20		100	---
G_{pe} η_C	V_{CE} = 28 V P_{out} = 125 W f = 400 MHz	8.0 50	8.5 55		dB %